



Micro Commercial Components  
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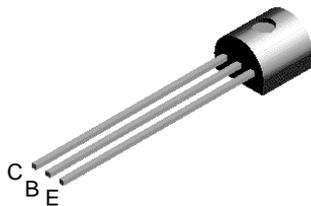
**S8550**

**PNP Silicon  
 Transistors**

**Features**

- TO-92 Plastic-Encapsulate Transistors
- Capable of 0.625Watts( $T_{amb}=25^{\circ}C$ ) of Power Dissipation.
- Collector-current 0.5A
- Collector-base Voltage 40V
- Operating and storage junction temperature range:  $-55^{\circ}C$  to  $+150^{\circ}C$
- Marking Code: S8550

Pin Configuration



Electrical Characteristics @  $25^{\circ}C$  Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ( $I_C=100\mu A$ , $I_E=0$ )	40	---	Vdc
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ( $I_C=0.1mA$ , $I_B=0$ )	25	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ( $I_E=100\mu A$ , $I_C=0$ )	5.0	---	Vdc
$I_{CBO}$	Collector Cutoff Current ( $V_{CB}=40Vdc$ , $I_E=0$ )	---	0.1	$\mu A$
$I_{CEO}$	Collector Cutoff Current ( $V_{CE}=20Vdc$ , $I_B=0$ )	---	0.2	$\mu A$
$I_{EBO}$	Emitter Cutoff Current ( $V_{EB}=3.0Vdc$ , $I_C=0$ )	---	0.1	$\mu A$

ON CHARACTERISTICS

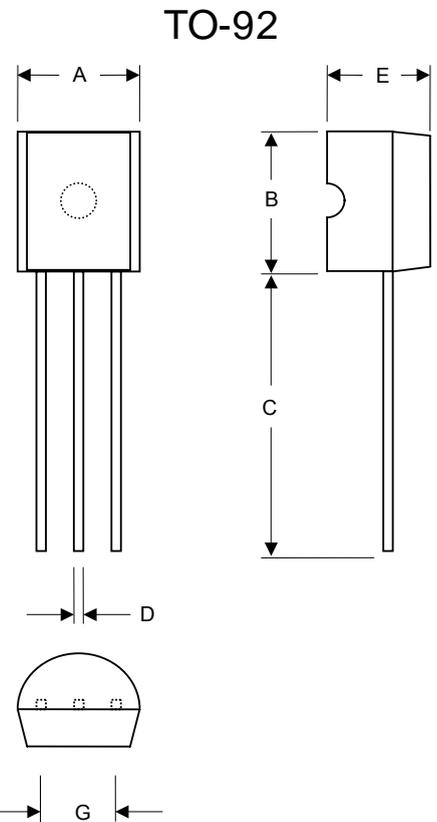
$h_{FE(1)}$	DC Current Gain ( $I_C=50mA$ , $V_{CE}=1.0Vdc$ )	85	300	---
$h_{FE(2)}$	DC Current Gain ( $I_C=500mA$ , $V_{CE}=1.0Vdc$ )	40	---	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ( $I_C=500mA$ , $I_B=50mA$ )	---	0.6	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ( $I_C=500mA$ , $I_B=50mA$ )	---	1.2	Vdc
$V_{EB}$	Base- Emitter Voltage ( $I_E=100mA$ )	---	1.4	Vdc

SMALL-SIGNAL CHARACTERISTICS

$f_T$	Transistor Frequency ( $I_C=20mA$ , $V_{CE}=6.0Vdc$ , $f=30MHz$ )	150	---	MHz
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CLASSIFICATION OF  $h_{FE(1)}$

Rank	B	C	D
Range	85-160	120-200	160-300



DIM	DIMENSIONS				NOTE
	INCHES		MM		
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	